

<b>Notice of References Cited</b>	Application/Control No. 09/936,818	Applicant(s)/Patent Under Reexamination TAKAHASHI ET AL.	
	Examiner Matthew J. Song	Art Unit 1722	Page 1 of 1

**U.S. PATENT DOCUMENTS**

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-5,956,364	09-1999	Jiang et al.	372/96
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	EP 864672 A2	09-1998	European Patent	HOOPER et al.	C30B 23/02
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**NON-PATENT DOCUMENTS**

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	U	Yang et al., "High-quality GaN and AlN grown by gas-source molecular beam epitaxy using ammonia as the nitrogen source", J. Vac. Sci. Technol. B 14(3), May/June 1996, pg 2354-2356.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.